# MT2306

# N-Channel Enhancement Mode Field Effect Transistor

# **Product Summary**

PRODUCT SUMMARY						
Vdss	Id	$Rds(ON)$ $(m \Omega)$ $Typ$				
20V	4.0A	46 @ VGS=10V				
	4.0A	65@ VGS=4.5V				

## **Features**

- Super high dense cell design for low RDS(ON)
- · Rugged and reliable
- · Simple drive requirement

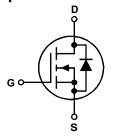
# **Applications**

· LED Display

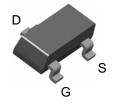


http://www.mtsemi.com

## **Simplified Schematic**



MARKING DIAGRAM & PIN ASSIGNMENT



**SOT-23** 

# **Absolute Maximum Ratings**(T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	20	V
Gate-Source Voltage	VGS	12	V
Drain Current-Continuous <sup>a</sup> @Tj=125 ℃	Id	4.0	A
- Pulse $d^b$	Ідм	10	A
Drain-source Diode Forward Current <sup>a</sup>	Is	1.25	A
Maximum Power Dissipation <sup>a</sup>	PD	1.25	W
Operating Junction and Storage Temperature Range	Tj,Tstg	-55 to 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient <sup>a</sup>	Rth JA	100	°C/W
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# ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

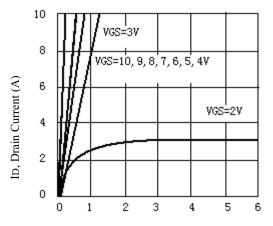
Parameter	Symbol	Symbol Condition		Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V,I <sub>D</sub> =250µA	20			V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V			1	μД
Gate-Body Leakage	Igss	V <sub>GS</sub> =±8V,V <sub>DS</sub> =0V			±100	nA
ON CHARACTERITICS						
Gate Threshold Voltage	V <sub>G</sub> s(th)	VDS=VGS,ID=250µA	0.5	0.8	1.5	V
D : 0 0 0 1 D : 1	D	V <sub>G</sub> S=4.5V,I <sub>D</sub> =2.8A		46	55	
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =2.5V,I <sub>D</sub> =2.0A		65	76	mΩ
Forward Transconductance	gFS	V <sub>GS</sub> =7V,I <sub>D</sub> =5A		5		S
DAYNAMIC CHARACTERISTICS				l	1	
Input Capacitance	Ciss			608		pF
Output Capacitance	Coss	Coss Vds=10V,Vgs=0V f=1.0MHz		115		pF
Reverse Transfer Capacitance	Crss	1 1.011112		86		pF
SWITCHING CHARACTERISISTICS						,
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =10V		10		ns
Rise Time	tr	ID=3.6A,		14		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>	V <sub>GEN</sub> =4.5V R <sub>L</sub> =10ohm		39		ns
Fall Time	tf	RGEN=10ohm		26		ns
Total Gate Charge	Qg			9.2		nC
Gate-Source Charge	Qgs	$V_{DS}=10V,I_{D}=1A$ $V_{GS}=4.5V$		1.6		nC
Gate-Drain Charge	Qgd	v GS-4.3 v		2.6		nC

# ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted)

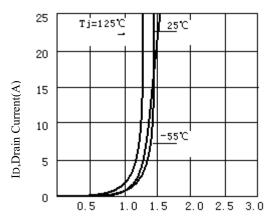
Parameter	Symbol	Min	Тур	Max	Unit		
DRAIN-SOURCE DIODE CHARACTERISTICS							
Diode Forward Voltage	Vsd	V <sub>G</sub> S=0V,I <sub>S</sub> =1.25A		0.84	1.3	V	

#### Notes

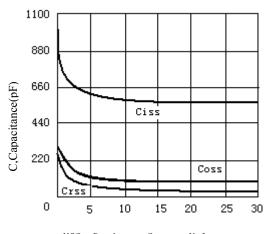
- a. Surface Mounted on FR4 Board, t≤10sec
- b. Pulse Test: Pulse Width ≤ 300Us, Duty Cycle ≤ 2%
- c. Guaranteed by design, not subject to production testing.



VDS, Drain-to-Source Voltage (V) Figure 1.Output Characteristics



VGS, Gate-to-source Voltage (V) Figure 2. Transfer Characteristics



VGS, Drain-to Source Voltage

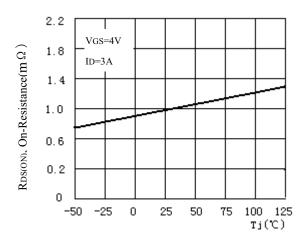
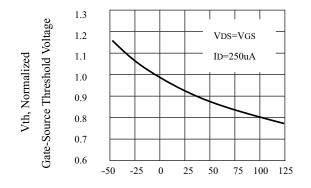
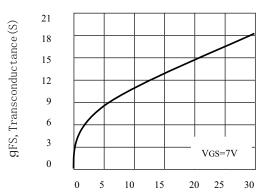


Figure 4. On-Resistance Variation with Temperature

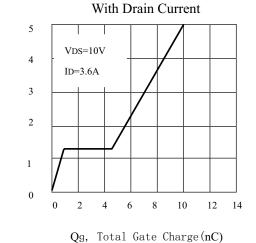
Figure 3. Capacitance



Tj., Junction Temperature( $^{\circ}$ C)
Figure 5. Gate Threshold Variation
With Temperature

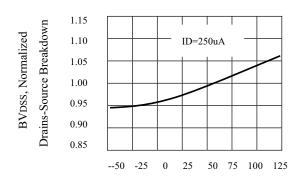


IDS, Drain-Source Current (A)
Figure 7. Transconductance Variation

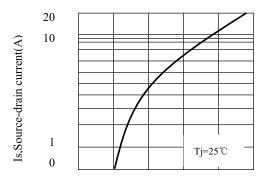


VGS, Gate to Source Voltage

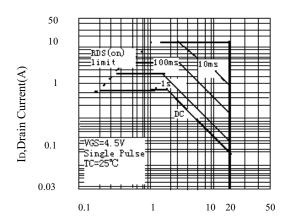
Figure 9. Gate Charge



 $Tj, \ Junction \ Temperature \ (^{\mathbb{C}})$   $Figure 6. Breakdown \ Voltage \ Variation$   $With \ Temperature$ 



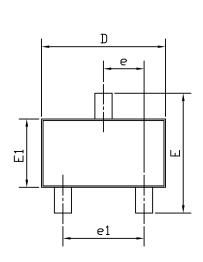
Vsp, Body Diode Forward Voltage
Figure 8. Body Diode Forward Voltage
Variation with Source Current

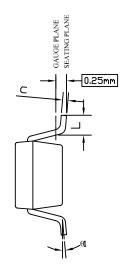


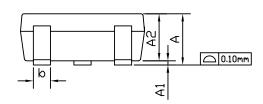
VDS, Drain-Source Voltage(V)
Figure 10.Maximum Safe Operating Area

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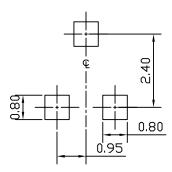
# SOT23 PACKAGE OUTLINE







#### RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENS	IONS IN MILLI	METERS	DIMENSIONS IN INCHES			
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85		1.25	0.033		0.049	
A1	0.00		0.13	0.000		0.005	
A2	0.70	1.00	1.15	0.028	0.039	0.045	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.08	0.13	0.20	0.003	0.005	0.008	
D	2.80	2.90	3.10	0.110	0.114	0.122	
Е	2.60	2.80	3.00	0.102	0.110	0.118	
E1	1.40	1.60	1.80	0.055	0.063	0.071	
e		0.95 BSC		0.037 BSC			
el		1.90 BSC		0.075 BSC			
L	0.30		0.60	0.012		0.024	
θ1	0°	5°	8°	0°	5°	8°	

#### NOTE

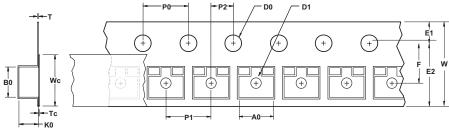
- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE  $\pm 0.100$  mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.

#### **SOT-23 Std Tape and Reel Data** SOT23-3L Packaging Configuration: Figure 1.0 Packaging Description: Packaging Description: SOT23-31. parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177mm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and so me other options are described in the Packaging Information table. Antistatic Cover Tape described in the Fackaging information table. These full freels are individually labeled and placed inside as tandard immediate box made of recyclable corrugated brown paper with a Fairchild logo printing. One box contains five reels maximum. And these immediate boxes are placed inside a labeled is hipping box which comes in different sizes depending on the number of parts shipped. PartNO.Label E mbosse d Carri er Tape 0091 0 SOT23-3L Packaging Information S tandar d Packaging Option D87Z SOT23-3L Unit Orientation Packaging type TNR TNR Qty per Reel/Tube/Bag 3,000 10,000 Reel Size 7" Dia 13" Box Dimension (mm) 193x 183 x80 355x 333 x 40 MARKING DIAGRAM Max qty per Box 15,000 30,000 00 X Weight per unit (gm) 0.0082 0.0082 Weight per Reel (kg) 0.1175 0.4006 Note/Comments X:Month Code X:Year Code Barcode 00: Manufacturer ID Lab el Barcode Labels ample XH1 MT2306ACTR QTY: 3000 MOS-TECH SEMICONDUCTOR LTD (ACTR) 193m m x 183m m x 80m m Pizza B ox for S tandard O ption SOT23-3L Tape Leader and Trailer Configuration: Figure 2.0 $\bigcirc$ 0 0 0 ComponentsTrailer Ta pe 300mm minimum or Leade r T ape 500mm minimum or 75 em pty pockets 125 empty pockets

## SOT-23 Std Tape and Reel Data, continued

#### **SOT23-3L Embossed Carrier Tape**

Configuration: Figure 3.0



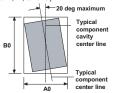
User Direction of Feed	

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

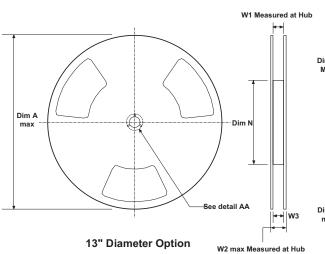


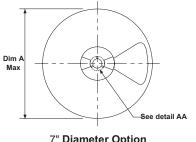
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

# SOT23-3L Reel Configuration: Figure 4.0





	7" Diameter Option
	→ B Min
Dim D min	Dim C
	DETAIL AA

Dimensions are in inches and millimeters										
Tape Size	Size         Reel Option         Dim A         Dim B         Dim C         Dim D         Dim N         Dim W1         Dim W2         Dim W3 (LSL)								Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9	

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